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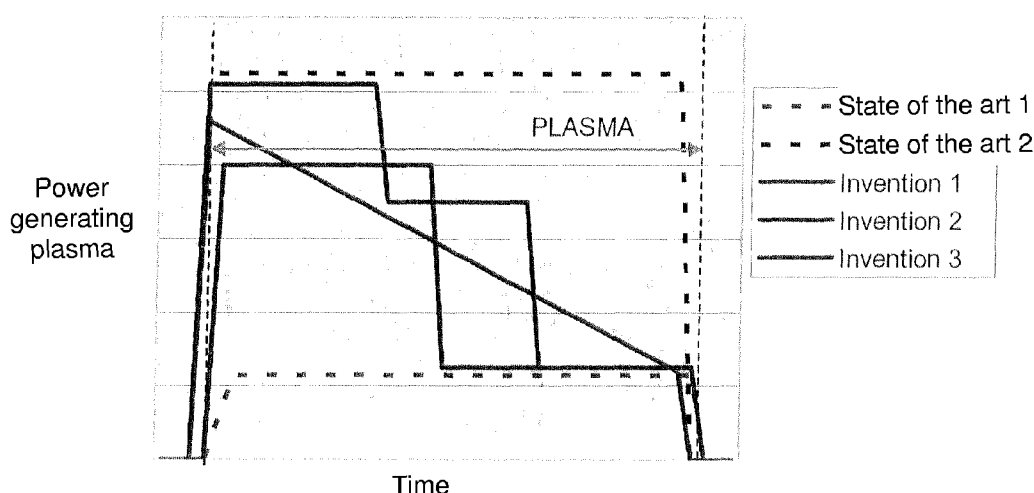
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(54) Title: A METHOD OF BONDING TWO WAFERS MADE OUT OF MATERIALS SELECTED FROM SEMICONDUCTOR MATERIALS



(57) Abstract: The invention relates to a method of bonding together two wafers made of materials selected from semiconductor materials, said method implementing plasma activation of the surface of at least one of the two wafers to be bonded together, and comprising, during plasma activation, controlling the activation parameters to modify the kinetic energy of the species contained in the plasma in order to create a disturbed region of controlled thickness in the thickness of a surface region of the wafer whose surface is being activated.

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